PNP/NPN Epitaxial Planar Silicon Transistors



2SB1203/2SD1803

High-Current Switching Applications

Applications

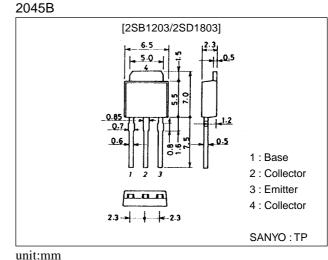
• Relay drivers, high-speed inverters, converters, and other general high-current switching applications.

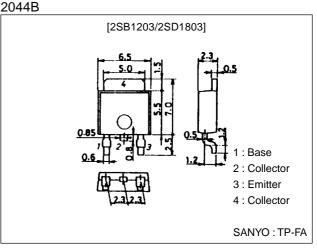
Features

- \cdot Low collector-to-emitter saturation voltage.
- \cdot High current and high f_T .
- · Excellent linearity of h_{FE}.
- · Fast switching speed.
- Small and slim package making it easy to make 2SB1203/2SD1803-applied sets smaller.

Package Dimensions

unit:mm





- Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.
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():2SB1203

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)60	V
Collector-to-Emitter Voltage	VCEO		(–)50	V
Emitter-to-Base Voltage	VEBO		(–)6	V
Collector Current	۱C		(–)5	A
Collector Current (Pulse)	I _{CP}		(–)8	A
Collector Dissipation	PC		1	W
		Tc=25°C	20	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

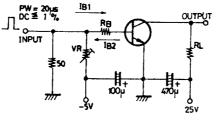
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)40V, I _E =0			(–)1	μA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)1	μA
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)0.5A	70*		400*	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)4A	35			
Gain-Bandwidth Product	fT	V _{CE} =(-)5V, I _C =(-)1A		(130)		MHz
				180		MHz
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(60)40		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)3A, I _B =(-)0.15A		220	400	mV
				(-280)	(550)	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)3A, I _B =(-)0.15A		()0.95	(–)1.3	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μA, I _E =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(–)50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)10μA, I _C =0	(–)6			V
Turn-ON Time	ton	See specified Test Circuit		50(50)		ns
Storage Time	t _{stg}	See specified Test Circuit		(450)		ns
				500		ns
Fall Time	t _f	See specified Test Circuit		(20)20		ns

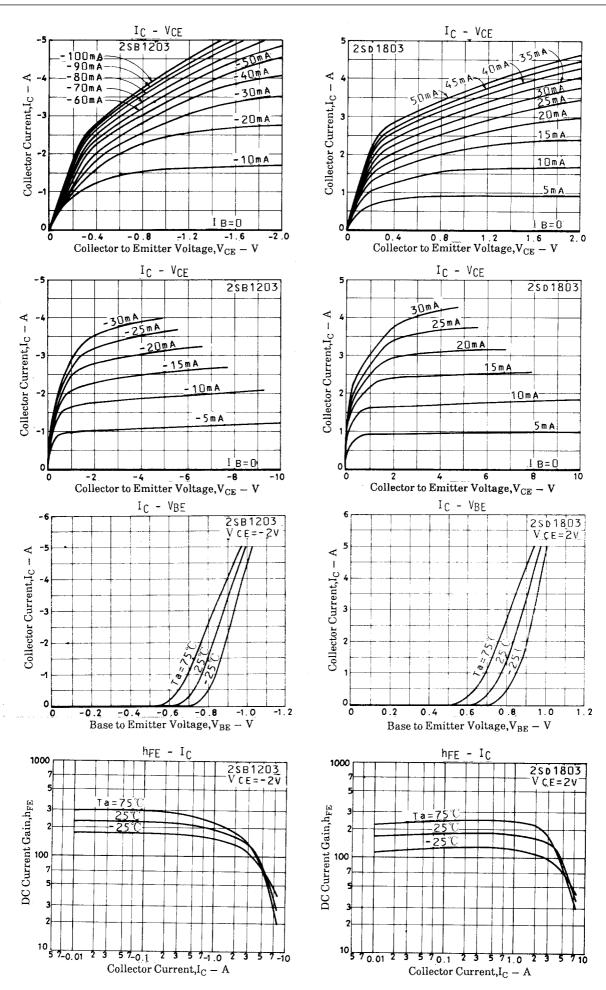
 \ast : The 2SB1203/2SD1803 are classified by 0.5A h_{FE} as follows :

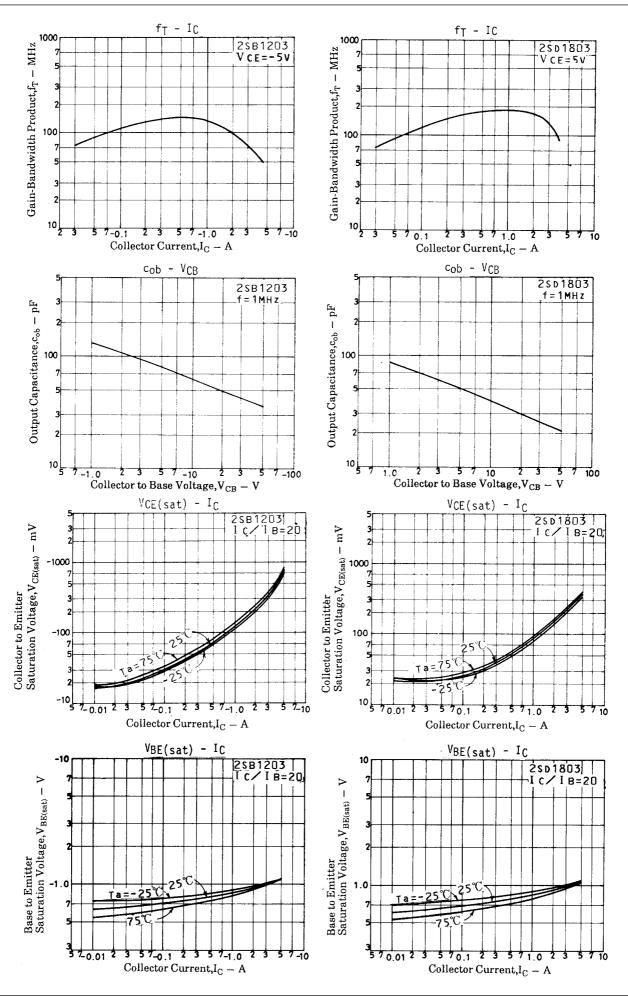
70 Q 140 100 R 2	140 S 280	200 T 400
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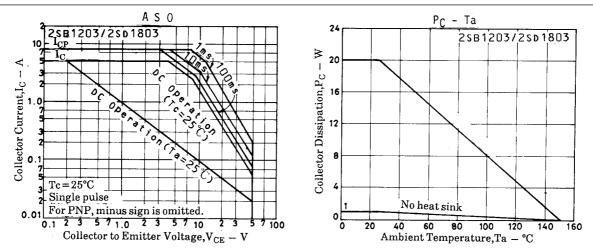
Switching Time Test Circuit



I C=10 I B1=-10 I B2=2A (For PNP, the polarity is reversed.) Unit (resistance : Ω, capacitance : F)







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